

Silicon NPN Power Transistors

2SC2612

DESCRIPTION

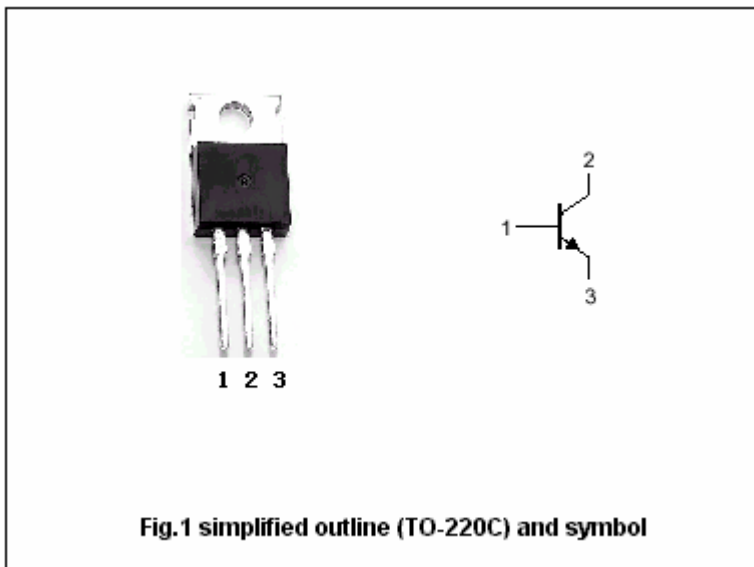
- With TO-220 package
- High collector breakdown voltage
: $V_{CEO}=400V(\text{Min})$

APPLICATIONS

- For high voltage ,high speed and high power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		3	A
I_{CM}	Collector current-Peak		6	A
I_B	Base current		1.5	A
P_T	Total power dissipation	$T_C=25$	30	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A, R _{BE} =, L=100mH	400			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.5A; I _B =0.3A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1.5A; I _B =0.3A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =400V; I _E =0			100	μA
I _{CEO}	Collector cut-off current	V _{CE} =350V; R _{BE} =			100	μA
h _{FE-1}	DC current gain	I _C =1.5A; V _{CE} =5V	15			
h _{FE-2}	DC current gain	I _C =3A; V _{CE} =5V	7			
Switching times						
t _{on}	Turn-on time	I _C =3.0A I _{B1} = I _{B2} =0.6A V _{CC} 150V			1.0	μs
t _{stg}	Storage time			1.2	2.5	μs
t _f	Fall time				1.0	μs

PACKAGE OUTLINE

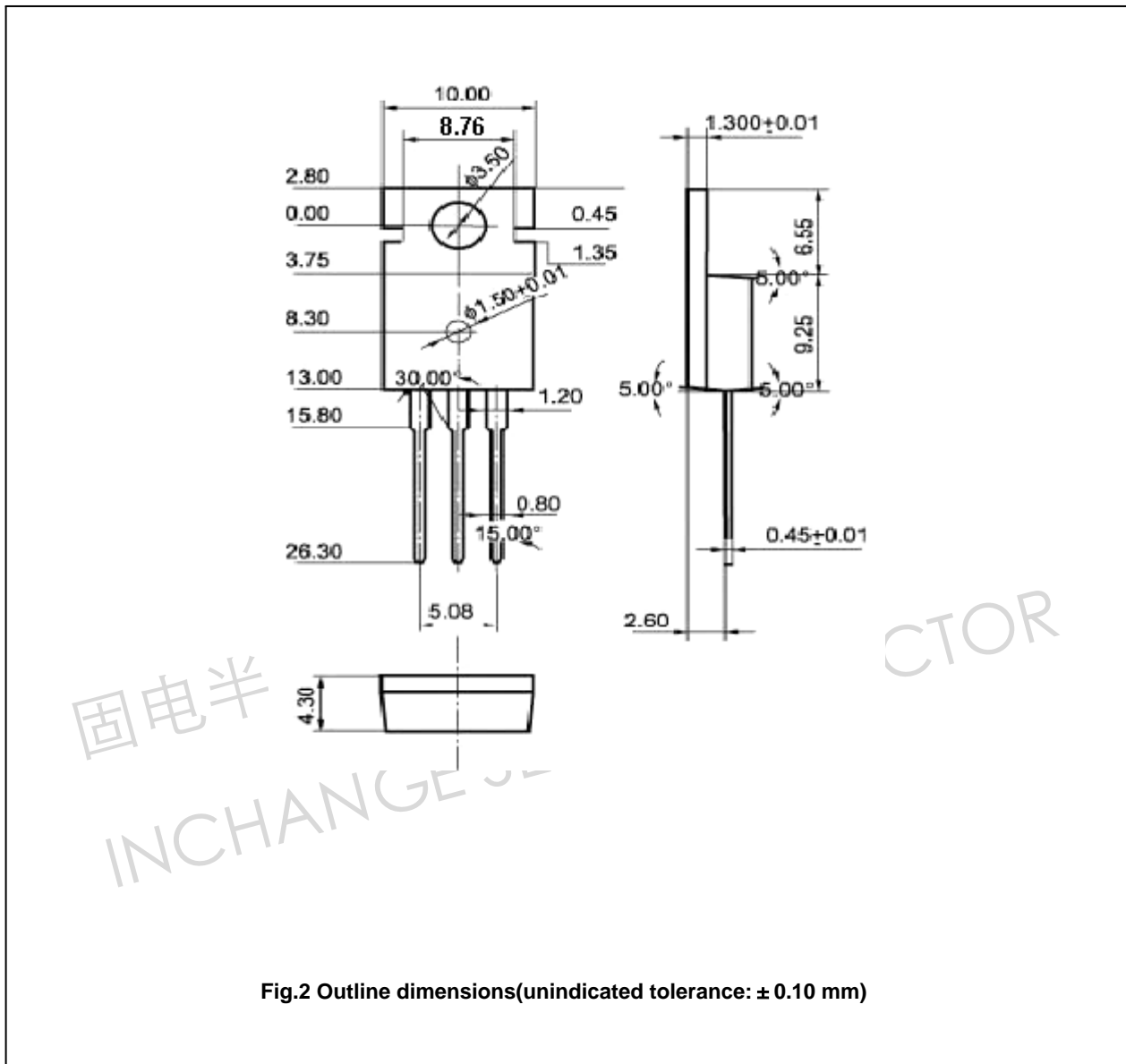


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)

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